



TSM2302

20V N-Channel MOSFET

SOT-23



Pin Definition:

- 1. Gate
- 2. Source
- 3. Drain

Key Parameter Performance

Parameter		Value	Unit	
V_{DS}		20	V	
R _{DS(on)} (max)	$V_{GS} = 4.5V$	65	m	
	$V_{GS} = 2.5V$	95		
Q _g		5.4	nC	

Features

Advance Trench Process Technology High Density Cell Design for Ultra Low On-resistance

Application

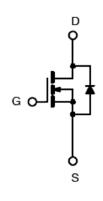
Load Switch PA Switch

Ordering Information

Part No.	Package	Packing		
TSM2302CX RF	SOT-23	3kpcs / 7+Reel		
TSM2302CX RFG	SOT-23	3kpcs / 7+Reel		

Note: %G+denotes for Halogen- and Antimony-free as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds

Block Diagram



N-Channel MOSFET

Absolute Maximum Ratings (T_C = 25°C, unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V_{DS}	20	V	
Gate-Source Voltage		V_{GS}	±8	V	
Continuous Drain Current		I _D	2.8	А	
Pulsed Drain Current (Note 1)		I _{DM}	8	А	
Continuous Source Current (Diode Conduction) (Note 2)		I _S	1.6	А	
Maximum Power Dissipation	Ta = 25°C	0	1.25	W	
	Ta = 75°C	P _D	0.8		
Operating Junction and Storage Temperature Range		T_{J}, T_{STG}	-55 to +150	°C	

Thermal Performance

Parameter	Symbol	Limit	Unit	
Thermal Resistance Junction to Foot	R _{JF}	75	°C/W	
Thermal Resistance Junction to Ambient	R _{JA}	145	°C/W	



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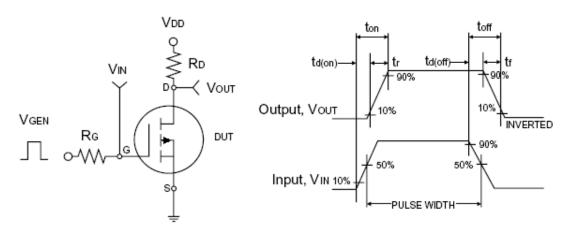


Electrical Specifications

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static ^(Note 3)		1				l
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250uA$	BV _{DSS}	20			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250uA$	V _{GS(TH)}	0.65	0.95	1.2	V
Gate Body Leakage	$V_{GS} = \pm 8V$, $V_{DS} = 0V$	I _{GSS}			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 16V, V_{GS} = 0V$	I _{DSS}			1.0	μA
On-State Drain Current	$V_{DS} = 5V, V_{GS} = 4.5V$	I _{D(ON)}	6			Α
Drain-Source On-State Resistance	$V_{GS} = 4.5V, I_D = 2.8A$	Ь		40	65	m
	$V_{GS} = 2.5V, I_D = 2.0A$	R _{DS(ON)}		50	95	
Forward Transconductance	$V_{DS} = 5V, I_{D} = 2.8A$	g fs		10		S
Diode Forward Voltage	$I_S = 1.6A, V_{GS} = 0V$	V_{SD}		0.76	1.2	V
Dynamic ^(Note 4)						
Total Gate Charge	$V_{DS} = 10V, I_D = 2.8A,$ $V_{GS} = 4.5V$	Q_g		5.4	10	
Gate-Source Charge		Q_gs		0.65		nC
Gate-Drain Charge		Q_gd		1.4		<u> </u>
Input Capacitance	\/ 40\/ \/ 0\/	C_{iss}		340		
Output Capacitance	$V_{DS} = 10V, V_{GS} = 0V,$ f = 1.0MHz	C_{oss}		115		pF
Reverse Transfer Capacitance		C_{rss}		33		
Switching ^(Note 5)						
Turn-On Delay Time	$V_{DD} = 6V, R_L = 10$, $I_D = 1A, V_{GEN} = 4.5V,$ $R_G = 6$	t _{d(on)}		12	25	
Turn-On Rise Time		t _r		36	60	no
Turn-Off Delay Time		t _{d(off)}		34	60	ns
Turn-Off Fall Time		t _f	1	10	25	

Notes:

- 1. Pulse width limited by the maximum junction temperature
- 2. Surface Mounted on FR4 Board t m5 sec.
- 3. Pulse test: PW m300µs, duty cycle m2%
- 4. For DESIGN AID ONLY, not subject to production testing.
- 5. Switching time is essentially independent of operating temperature.



Switching Test Circuit

Switchin Waveforms



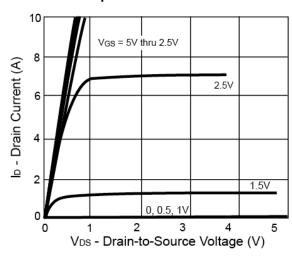
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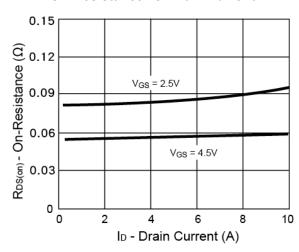


Electrical Characteristics Curve

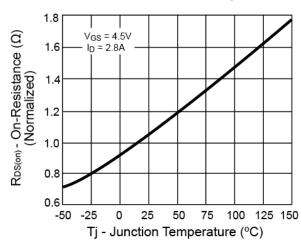
Output Characteristics



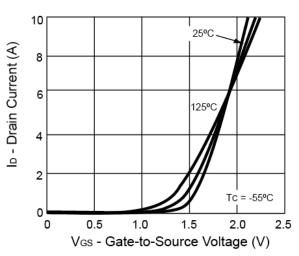
On-Resistance vs. Drain Current



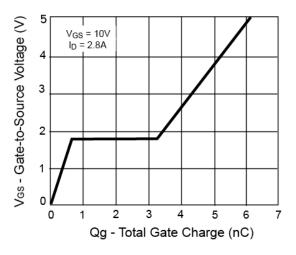
On-Resistance vs. Junction Temperature



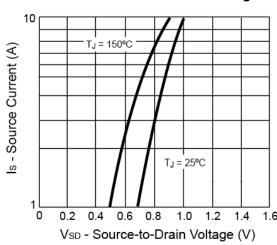
Transfer Characteristics



Gate Charge



Source-Drain Diode Forward Voltage



Version: C15

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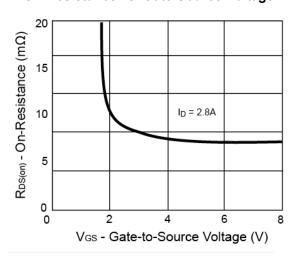
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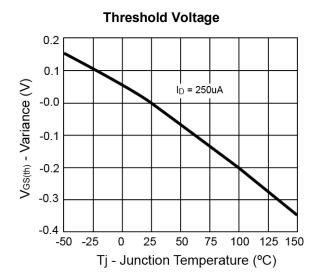
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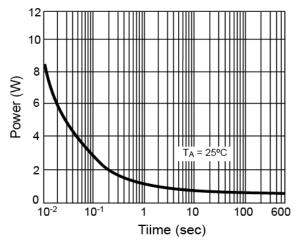
Electrical Characteristics Curve

On-Resistance vs. Gate-Source Voltage

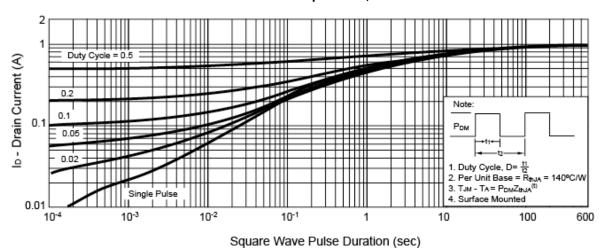




Single Pulse Power



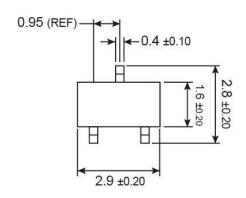
Normalized Thermal Transient Impedance, Junction-to-Ambient

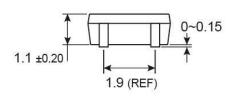


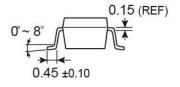




SOT-23 Mechanical Drawing

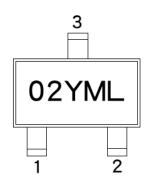






Unit: Millimeters

Marking Diagram



02 = Device Code

Y = Year Code

M = Month Code

(A=Jan, B=Feb, C=Mar, D=Apl, E=May, F=Jun, G=Jul, H=Aug,

I=Sep, J=Oct, K=Nov, L=Dec)
= Month Code for Halogen Free Product

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(O=Jan, P=Feb, Q=Mar, R=Apl, S=May, T=Jun, U=Jul, V=Aug, W=Sep, X=Oct, Y=Nov, Z=Dec)

L = Lot Code

Version: C15



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